## Adopted Levels

| | Type | Author | History Citation | Literature Cutoff Date |
|---|---|---|---|---|
| | Full Evaluation | C. W. Reich | NDS 113, 157 (2012) | 31-Dec-2010 |

$Q(\beta^-)=-10550$ (syst) *426*; S(n)=9733 (syst) *423*; S(p)=1417 (syst) *357*; $Q(\alpha)$=6450 *4*    2017Wa10
$Q(\varepsilon)$=9145 (syst) *299*; S(2n)=21967 (syst) *423*; S(2p)=969 (syst) *357*; $Q(\varepsilon p)$=9519 (syst) *299*    2017Wa10
Additional information 1.
Additional information 2.

### $^{159}$W Levels

| E(level) | $T_{1/2}$ | Comments |
|---|---|---|
| 0 | 7.3 ms *27* | $\%\alpha\approx99.9$; $\%\varepsilon+\%\beta^+\approx0.1$ |

$T_{1/2}$: from 1981Ho10.
$\%\alpha$: from the calculations of 1997Mo25, $T_{1/2}(\beta)$=0.37 s and $T_{1/2}(\alpha)$=0.28 ms, which corresponds to $\%\alpha$=99.9 and is adopted. Other: from 1973Ta30, the calculated $T_{1/2}(\varepsilon+\beta^+)$ ranges from 1 to 5 s, so the experimental $T_{1/2}$ corresponds to $\%(\varepsilon+\beta^+)$=0.15 to 0.73, which is in good agreement.
Assignment: Daughter of $^{163}$Os produced in $^{110}$Cd($^{58}$Ni,5n) established through position-time correlation following implantation in position-sensitive Si detector.